

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/747,600	12/29/2003	Hyuk Park	20063/OG03-037	6482	
34431 7	7590 08/27/2004		EXAMINER VU, DAVID		
GROSSMAN	& FLIGHT, LLC				
20 N. WACKE	ER DRIVE				_
SUITE 4220			ART UNIT	PAPER NUMBER	
CHICAGO II	60606		2010		

DATE MAILED: 08/27/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)				
		10/747,600	PARK ET AL.				
Office Action Sumn	nary	Examiner	Art Unit				
		DAVID VU	2818				
The MAILING DATE of this of Period for Reply	communication appe	ears on the cover sheet	with the correspondence add	lress			
A SHORTENED STATUTORY PE THE MAILING DATE OF THIS CO - Extensions of time may be available under the after SIX (6) MONTHS from the mailing date of - If the period for reply specified above is less ti - If NO period for reply is specified above, the n - Failure to reply within the set or extended peri Any reply received by the Office later than thre earned patent term adjustment. See 37 CFR	OMMUNICATION. provisions of 37 CFR 1.130 of this communication. nan thirty (30) days, a reply naximum statutory period will od for reply will, by statute, see months after the mailing	6(a). In no event, however, may within the statutory minimum of Il apply and will expire SIX (6) N cause the application to become	a reply be timely filed thirty (30) days will be considered timely. ONTHS from the mailing date of this cor ABANDONED (35 U.S.C. § 133).				
Status							
1) Responsive to communication	on(s) filed on 29 De	cember 2003					
2a)☐ This action is FINAL .		action is non-final.					
<u> </u>	• • •		atters, prosecution as to the	merits is			
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims							
4a) Of the above claim(s) 5) ☐ Claim(s) is/are allowe 6) ☐ Claim(s) <u>1,2 and 4-6</u> is/are r 7) ☐ Claim(s) <u>3,7 and 8</u> is/are ob							
Application Papers							
9)☐ The specification is objected 10)☒ The drawing(s) filed on 29 D Applicant may not request that Replacement drawing sheet(s) 11)☐ The oath or declaration is ob	ecember 2003 is/ar any objection to the d including the correction	e: a)□ accepted or b rawing(s) be held in abe on is required if the draw	vance. See 37 CFR 1.85(a). ng(s) is objected to. See 37 CF.	R 1.121(d).			
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a) All b) Some * c) No 1. Certified copies of the 2. Certified copies of the 3. Copies of the certified application from the Ir * See the attached detailed Off	ne of: priority documents priority documents copies of the priori nternational Bureau	have been received. have been received in ty documents have be (PCT Rule 17.2(a)).	n Application No en received in this National S	Stage			
Attachment(s)							
1) Motice of References Cited (PTO-892) 2) Dotice of Draftsperson's Patent Drawing	Review (PTO-948)		w Summary (PTO-413) lo(s)/Mail Date				
3) Information Disclosure Statement(s) (PTo Paper No(s)/Mail Date 03/17/04.			of Informal Patent Application (PTO-	152)			

DETAILED ACTION

Drawings

1. Figures 1a-1b should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

2. Claims 1, 2 and 4-6 are rejected under 35 U. S. C. 102(e) as being anticipated by Prall et al. (US Pat. 6,624,024, herein after Prall).

Regarding claims 1 and 5, Prall discloses in figs. 3-5 a method of fabricating a memory cell and a memory cell structure comprising: forming a plurality of gate areas, the gate areas

Application/Control Number: 10/747,600 Page 3

Art Unit: 2818

including a gate oxide 16, a floating gate 18, an insulating layer 20, and a control gate 22 (fig. 3 and col. 4, lines 56-61); forming spacers 48 on sidewalls of the gate areas to isolate and protect a gate area including a floating gate and a control gate (col. 5, lines 15-27); forming a gap filling layer 50 over a substrate including the gate area and the spacers (fig. 5 and col. 5, lines 36-40); and depositing an insulating layer 52 over the gate areas and the gap filling layer (col. 5, lines 41-43).

Regarding claims 2 and 6, Prall discloses that the spacers 48 are formed by depositing and etching a SiN layer (col. 5, lines 15-27).

Regarding claim 4, Prall discloses that the insulating layer 52 is formed of BPSG (borophosphorsilicate glass) (col. 5, lines 41-43).

Allowable Subject Matter

3. Claims 3, 7, 8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record does not disclose or suggest, either singularly or in combination at least the limitation of "the gap filling layer is formed of undoped polysilicon or amorphous silicon" as recited in claims 3 and 7.

₹

Application/Control Number: 10/747,600

Art Unit: 2818

Conclusion

Page 4

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Vu whose telephone number is (571) 272-1798. The examiner can normally be reached on Monday-Friday from 8:00am to 5:00pm. If attempt to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR, Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

David Vu

August 13, 2004

Ghulard